## ABSTRACT

## STABILITY OF THE S-N BOND IN S-NITROSOTHIOLS: COMPUTATIONAL AND EXPERIMENTAL APPROACH

Rustam S. Sabitov

Marquette University, 2024

S-Nitrosothiols (RSNOs) are chemical compounds capable to transport nitric oxide (NO) and show promise in the treatment of cardiovascular diseases. RSNOs occur naturally *in-vivo*, and others have been synthesized *in-vitro* as potential drug candidates for NO transport and release. However, RSNOs are inherently unstable due to their weak S–N bond  $(D_0(S-N)=25-30 \text{ kcal/mol})$ , so developing a deeper understanding of the factors influencing the RSNOs stability is crucial.

In Chapter 2, we investigated the substituent effect on the -SNO group properties. Substituting R– in RSNOs with more electro-donating character can stabilize the –SNO group according to the Natural Resonance Theory (NRT). But modeling the RSNOs is a complex task requiring usage of  $CCSD(T)/CBS_{0}$ . 5) or CCSD(T)-F12a/CBS<sub>(T-O)</sub> methods with the inclusion of different corrections (core-valence( $\Delta$ CV), scalar relativistic( $\Delta$ SR), spin-spin coupling( $\Delta$ SO), and high order corrections( $\Delta$ HO)) to predict properties of RSNOs accurately, specifically  $r(S-N)$  and  $D_0(S-N)$ . Here, H-SNO, H<sub>3</sub>C-SNO, H<sub>3</sub>Si-SNO were studied <sub>5)</sub> or CCSD(T)-F12a/CBS<sub>(T-Q)</sub> methods with the inclusion of different corrections (core-valence(ΔCV), scalar relativistic( $\Delta$ SR), spin-spin coupling( $\Delta$ SO), and high order corrections( $\Delta$ HO)) to predict properties o various basis sets, *cc-pVnZ-F12* and *aug-cc-pV(n+d)Z* (where n=D, T, Q and 5 (for *aug-cc-pV(5+d)Z*) with the addition of various corrections to correlation effects (ΔCV, ΔSR, ΔSO, ΔHO). It was found that r(S–N) is longer in the cis-H<sub>3</sub>Si-SNO and cis-H-SNO than in the cis-H<sub>3</sub>C-SNO. Additionally,  $D_0(S-N)$  is higher in the cis-H3C-SNO than in the cis-H-SNO and cis-H3Si-SNO.

In Chapter 3, experimentally, Ph<sub>3</sub> SiSNO and i-Pr<sub>3</sub> SiSNO were synthesized and characterized at temperatures below –35 °C. These silicon-containing RSNOs are stable at –45 °C but begin to decompose above –41 °C. Variable-temperature NMR studies determined the rotational energy barrier for cis-trans isomerization of Ph<sub>3</sub> SiS<sup>15</sup> NO to be approximately 8.60 kcal/mol, which is 3–4 kcal/mol lower than for carbon-substituted RSNOs. UV-Vis spectroscopy and TD-DFT calculations supported the formation of these compounds. The EPR spectroscopy at 77 K was used to study the relatively stable  $Ph_3$  SiS and i- $Pr<sub>3</sub> SiS<sup>+</sup> radicals.$ 

In Chapter 4, DFT and NBO analyses provided insights into the electronic origins of the observed instability of silicon-substituted RSNOs. Hyperconjugative interactions, specifically  $n(S) \rightarrow \sigma^*(Si-H)$ , play a crucial role in modulating the properties of the -SNO group. Deletion of these interactions led to a decrease in the S–N bond length ( $\sim$ 0.05 Å) and an increase in bond dissociation energy, indicating that the silicon atom enhances interactions  $n(S) \rightarrow \sigma^*(Si-H)$  that weakens the S–N bond strength. A correlation was established between the electronegativity of the substituent and the S–N bond strength; increase in electronegativity decreases the bond strength due to increased hyperconjugative n(S)  $\rightarrow \sigma^*(R-X)$ interactions.

In Chapter 5, we are expanding investigation on the crucial influence of non-covalent interaction with  $\sigma$ -hole of Sulfur on stability of S-Nitrosothiols using the high-level ab initio and DFT methods. It was found that  $\pi$  systems can interact with -SNO group via  $\sigma$ -hole of sulfur. Such interaction promotes the partial double bond character in the S-N bond, or promotion of D resonance structure, and simultaneously reduces the ionic character of RS<sup>-</sup>/NO<sup>+</sup> (which destabilizes the -SNO group). Additionally, our calculation predicts that in the protein environment interaction of  $\pi$  systems with  $\sigma$ -hole of -SNO group tends to profoundly effect on the -SNO group properties (electronic structure and reactivity).